

Features

- N channel
- Enhancement mode
- Avalanche rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101
- Halogen-free according to IEC61249-2-21

Product Summary

Drain source voltage	V_{DS}	60	V
Drain-Source on-state resistance	$R_{DS(on)}$	0.12	Ω
Continuous drain current	I_D	2.9	A



Halogen-Free



Type	Package	Tape and Reel	Packaging
BSP320S	PG-SOT223	H6327: 1000pcs/r	Non dry
BSP320S	PG-SOT223	H6433: 4000pcs/r	Non dry

Maximum Ratings , at $T_J = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D	2.9	A
Pulsed drain current $T_A = 25^\circ\text{C}$	I_{Dpulse}	11.6	
Avalanche energy, single pulse $I_D = 2.9\text{ A}$, $V_{DD} = 25\text{ V}$, $R_{GS} = 25\ \Omega$	E_{AS}	60	mJ
Avalanche current, periodic limited by T_{jmax}	I_{AR}	2.9	A
Avalanche energy, periodic limited by T_{jmax}	E_{AR}	0.18	mJ
Reverse diode dv/dt $I_S = 2.9\text{ A}$, $V_{DS} = 20\text{ V}$, $di/dt = 200\text{ A}/\mu\text{s}$, $T_{jmax} = 150^\circ\text{C}$	dv/dt	6	kV/ μs
Gate source voltage	V_{GS}	± 20	V
Power dissipation $T_A = 25^\circ\text{C}$	P_{tot}	1.8	W
Operating temperature	T_i	-55 ... +150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ... +150	
IEC climatic category; DIN IEC 68-1		55/150/56	

Electrical Characteristics

Parameter at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified	Symbol	Values			Unit
		min.	typ.	max.	

Thermal Characteristics

Thermal resistance, junction - soldering point (Pin 4)	R_{thJS}	-	17	-	K/W
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ¹⁾	R_{thJA}	- - -	110 - -	- - 70	K/W

Static Characteristics

Drain- source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = 0.25\text{ mA}$	$V_{(BR)DSS}$	60	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 20\text{ }\mu\text{A}$	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current $V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25\text{ }^{\circ}\text{C}$ $V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 150\text{ }^{\circ}\text{C}$	I_{DSS}	- -	0.1 -	1 100	μA
Gate-source leakage current $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	-	10	100	nA
Drain-Source on-state resistance $V_{GS} = 10\text{ V}$, $I_D = 2.9\text{ A}$	$R_{DS(on)}$	-	0.09	0.12	Ω

¹ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics

Parameter at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Transconductance $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 2.9\text{ A}$	g_{fs}	2.5	5.8	-	S
Input capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	-	275	340	pF
Output capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	-	90	120	
Reverse transfer capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	-	50	65	
Turn-on delay time $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 2.9\text{ A}$, $R_G = 33\text{ }\Omega$	$t_{d(on)}$	-	11	17	ns
Rise time $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 2.9\text{ A}$, $R_G = 33\text{ }\Omega$	t_r	-	25	40	
Turn-off delay time $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 2.9\text{ A}$, $R_G = 33\text{ }\Omega$	$t_{d(off)}$	-	25	40	
Fall time $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 2.9\text{ A}$, $R_G = 33\text{ }\Omega$	t_f	-	35	55	

Electrical Characteristics

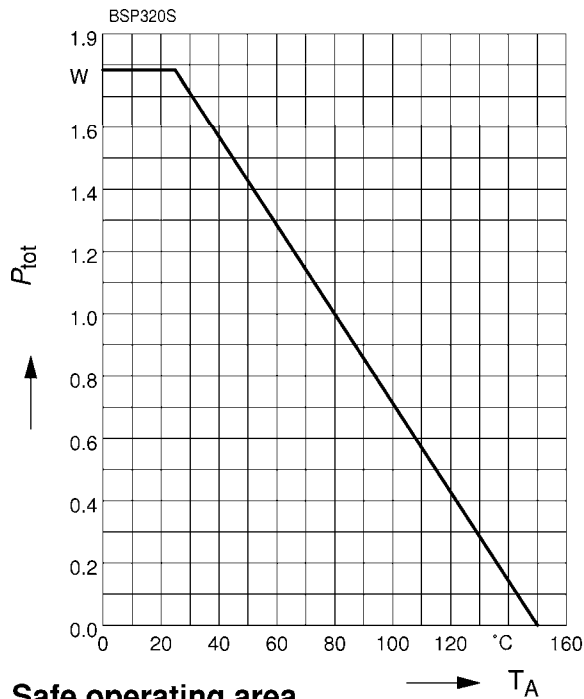
Parameter at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Gate charge at threshold $V_{DD} = 40\text{ V}$, $I_D = 0.1\text{ A}$, $V_{GS} = 1\text{ V}$	$Q_{G(th)}$	-	0.25	0.3	nC
Gate charge at $V_{gs}=7V$ $V_{DD} = 40\text{ V}$, $I_D = 2.9\text{ A}$, $V_{GS} = 0\text{ to }7\text{ V}$	$Q_{g(7)}$	-	7.4	9.3	nC
Gate charge total $V_{DD} = 40\text{ V}$, $I_D = 2.9\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$	Q_g	-	9.7	12	
Gate plateau voltage $V_{DD} = 40\text{ V}$, $I_D = 2.9\text{ A}$	$V_{(plateau)}$	-	4.7	-	V

Reverse Diode

Inverse diode continuous forward current $T_A = 25\text{ }^{\circ}\text{C}$	I_S	-	-	2.9	A
Inverse diode direct current,pulsed $T_A = 25\text{ }^{\circ}\text{C}$	I_{SM}	-	-	11.6	
Inverse diode forward voltage $V_{GS} = 0\text{ V}$, $I_F = 5.8\text{ A}$	V_{SD}	-	0.95	1.2	V
Reverse recovery time $V_R = 30\text{ V}$, $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	45	56	ns
Reverse recovery charge $V_R = 30\text{ V}$, $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	0.08	0.12	μC

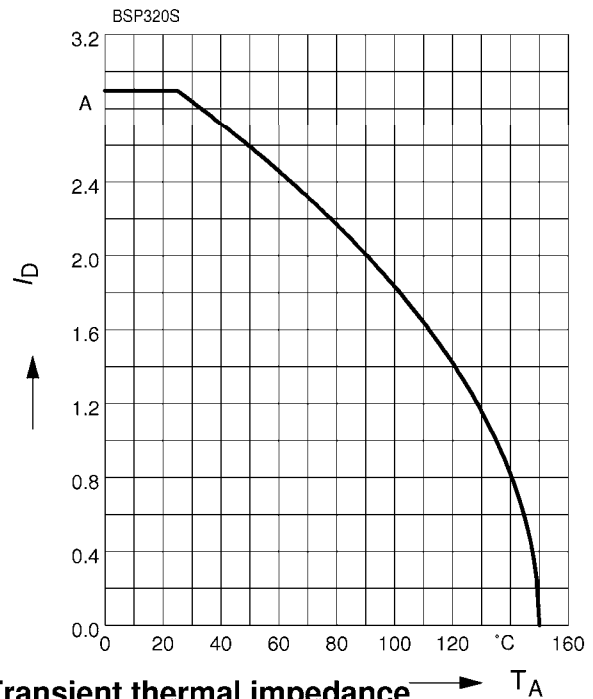
Power Dissipation

$$P_{\text{tot}} = f(T_A)$$



Drain current

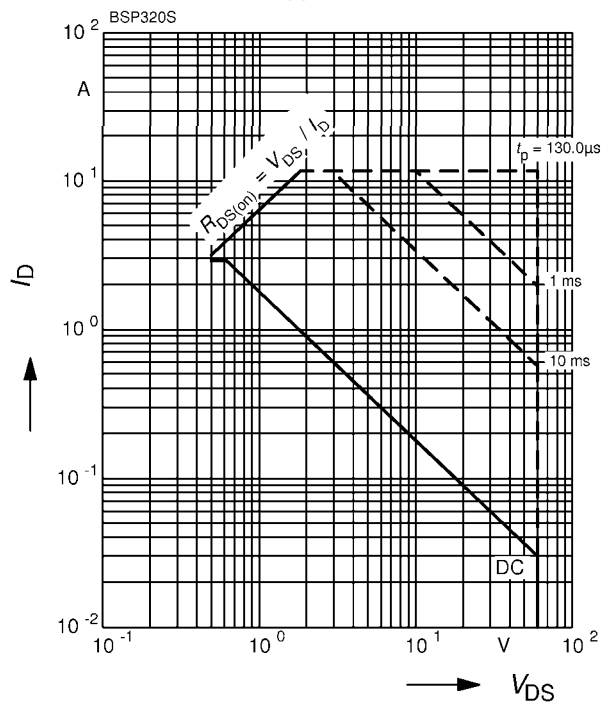
$$I_D = f(T_A)$$



Safe operating area

$$I_D = f(V_{DS})$$

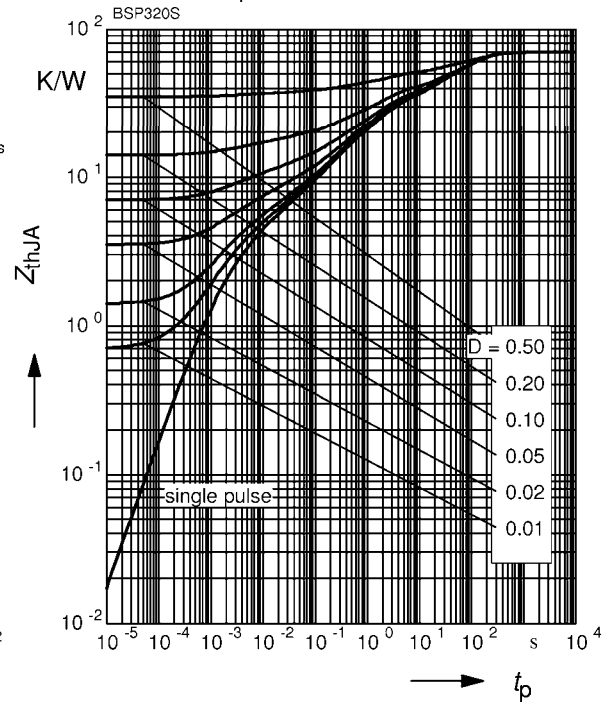
parameter : $D = 0$, $T_A = 25$ °C



Transient thermal impedance

$$Z_{\text{thJA}} = f(t_p)$$

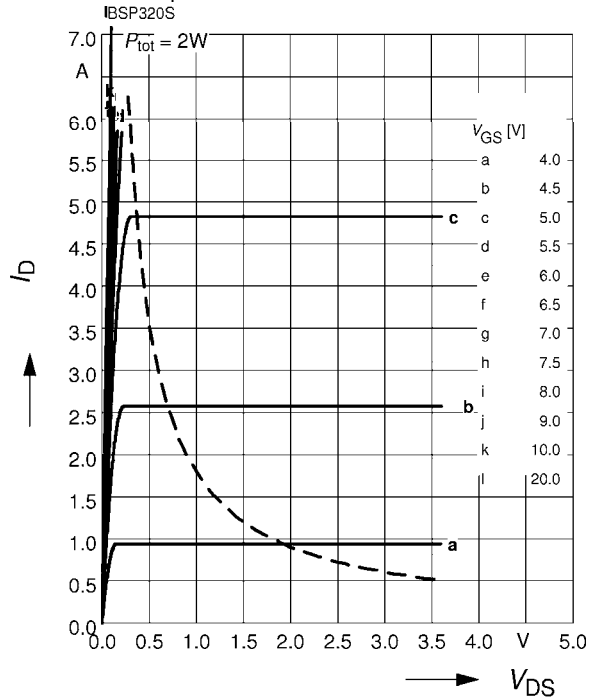
parameter : $D = t_p / T$



Typ. output characteristics

$$I_D = f(V_{DS})$$

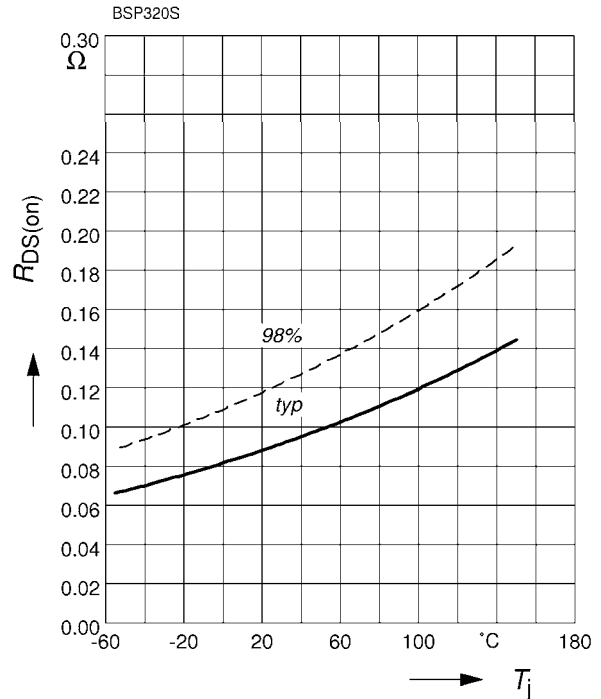
parameter: $t_p = 80 \mu s$



Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

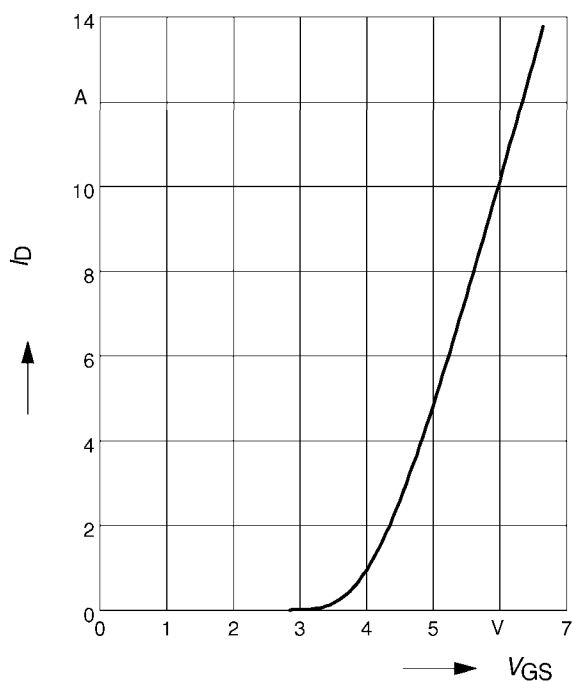
parameter: $I_D = 2.9 A$, $V_{GS} = 10 V$



Typ. transfer characteristics $I_D = f(V_{GS})$

parameter: $t_p = 80 \mu s$

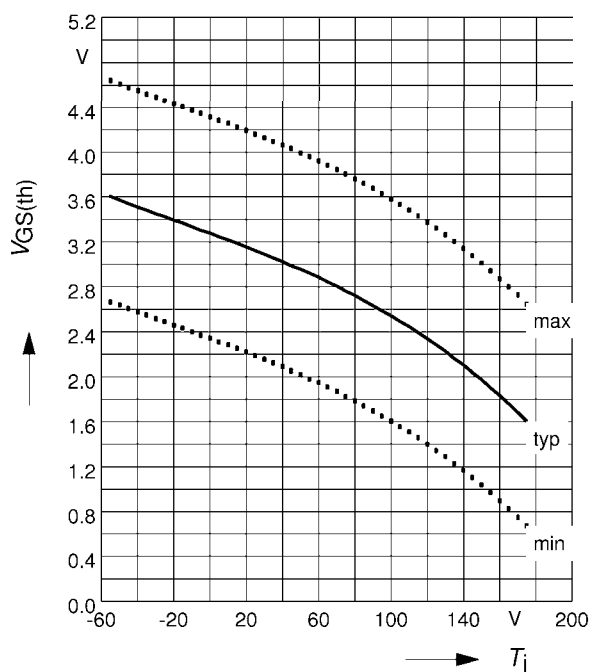
$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$



Gate threshold voltage

$V_{GS(th)} = f(T_j)$

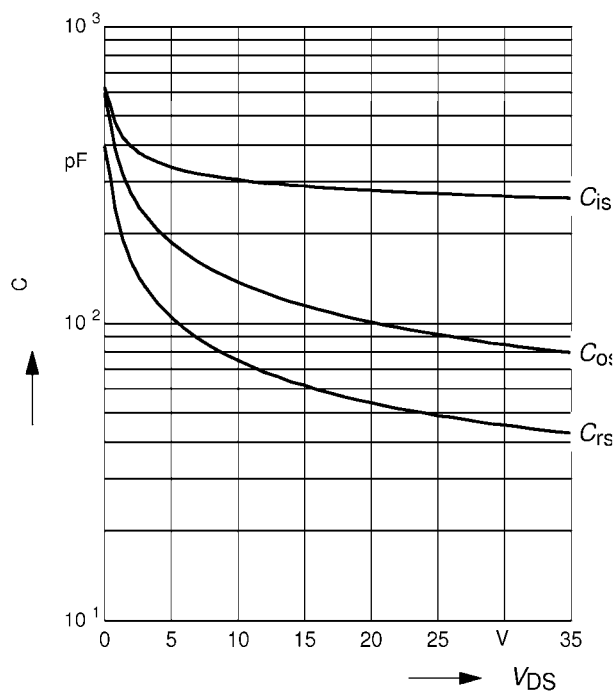
parameter: $V_{GS} = V_{DS}$, $I_D = 20 \mu A$



Typ. capacitances

$C = f(V_{DS})$

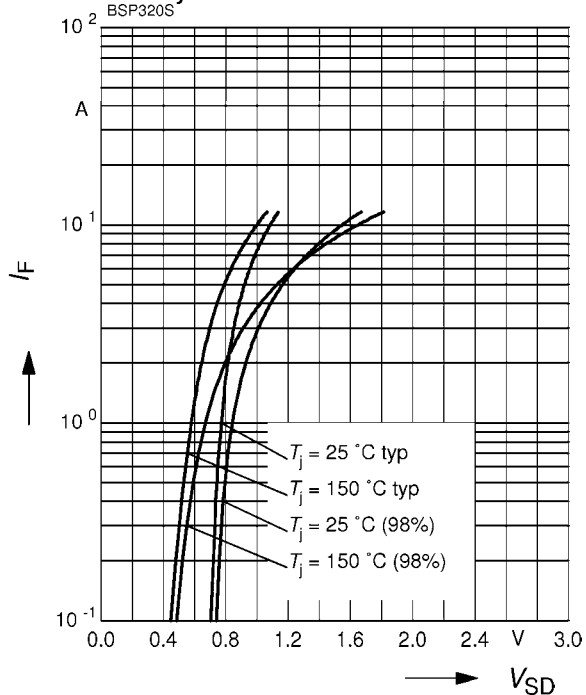
Parameter: $V_{GS} = 0 V$, $f = 1 MHz$



Forward characteristics of reverse diode

$I_F = f(V_{SD})$

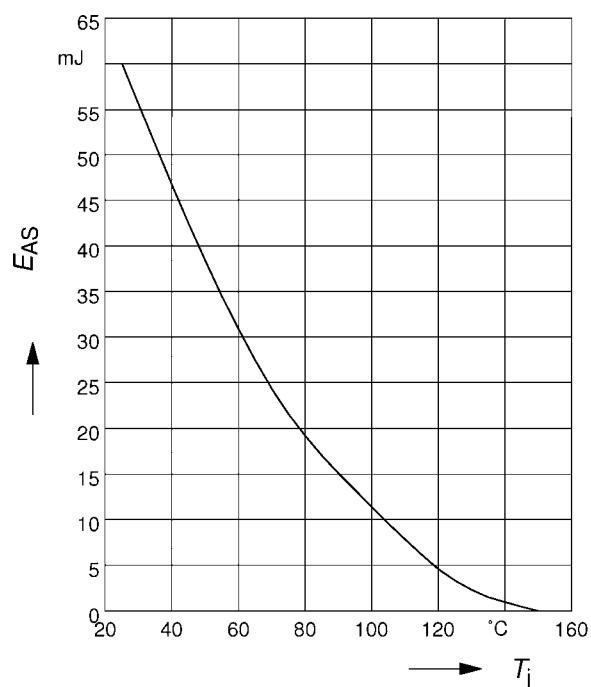
parameter: T_j , $t_p = 80 \mu s$



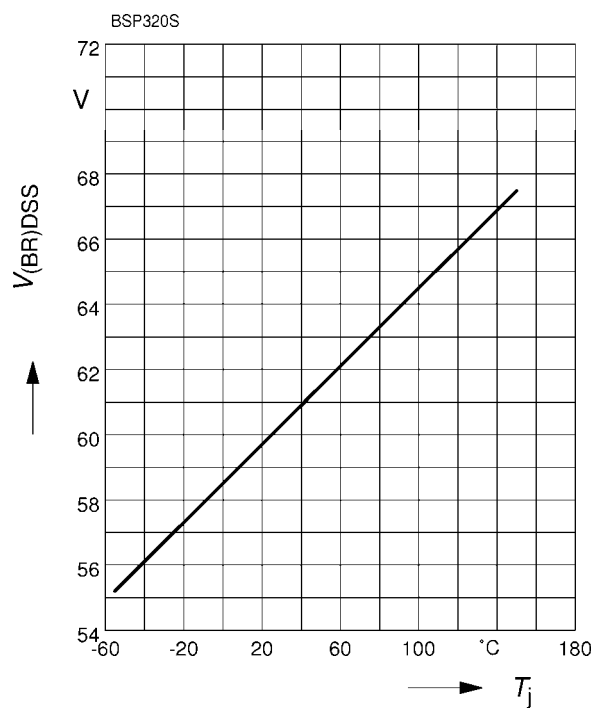
Avalanche Energy $E_{AS} = f(T_j)$

parameter: $I_D = 2.9\text{ A}$, $V_{DD} = 25\text{ V}$

$R_{GS} = 25\ \Omega$

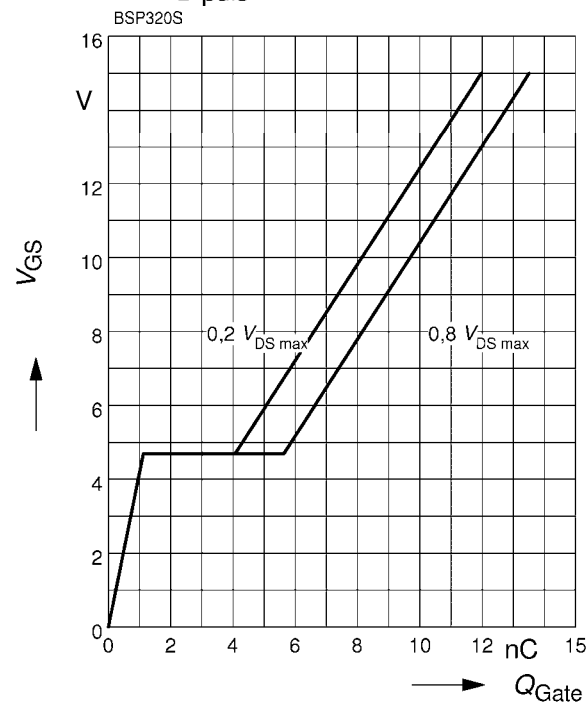

Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$


Typ. gate charge

$V_{GS} = f(Q_{Gate})$

parameter: $I_{D\text{ puls}} = 2.9\text{ A}$



Published by
Infineon Technologies AG
81726 Munich, Germany
© 2008 Infineon Technologies AG
All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.